

系 所：電機工程學系

考試科目：電子材料概論

考試日期：0205，節次：2

第1頁，共 1 頁

※ 考生請注意：本試題不可使用計算機。 請於答案卷(卡)作答，於本試題紙上作答者，不予計分。

1. Calculate the atomic packing factor (AFP) for the BCC unit, assuming the atoms to be hard spheres.(10%)
2. Draw the following direction vectors in cubic unit cells. (10%)
[100] , [110] , [112] , [-110] , [-32-1]
3. Please compare the effect of temperature and impurity respectively on the conductivity for metal, inorganic semiconductor, organic semiconductor and insulator. (20%)
4. a). What is polarization ? please describe all possible the polarization mechanisms .(10%)

b). What is Magnetization ? please describe all possible the magnetization mechanisms. (10%)
5. Calculate the number of silicon atoms per cubic meter. The density of silicon is 2.33 g/cm^3 , and its atomic mass is 28.08 g/mol .(10%)
6. Calculate the electrical resistivity of intrinsic silicon at 300K. For Si at 300K, $n_i=1.5\times10^{16} \text{ carriers/m}^3$, $q=1.6\times10^{-19}\text{C}$, $\mu_n=0.135\text{m}^2/\text{Vs}$, and $\mu_p=0.048\text{m}^2/\text{Vs}$ (10%)
7. 6 Please explain following noun: (20%)
 - a). Fermi energy
 - b). Schottky effect
 - c). Mean free path
 - d). Fick's first law
 - e). Fick's second law
 - f). Gibbs phase rule
 - g). Seebeck effect
 - h). Matthiessen's rule
 - i). Nordheim's rule
 - j). Skin depth